

30V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	35mΩ@10V	5.8A
	40mΩ@4.5V	
	52mΩ@2.5V	

Feature

TrenchFET Power MOSFET

Excellent $R_{DS(on)}$ and Low Gate Charge

EC-Q101 qualified (Automotive grade with suffix "Q".)

Expsemi electronics

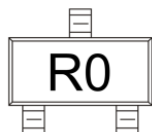
Application

DC/DC Converter

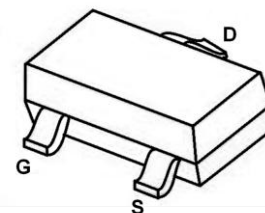
Load Switch for Portable Devices

Battery Switch

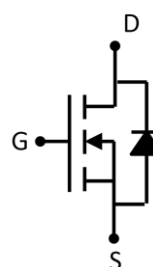
MARKING:



SOT-23



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	30	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient ⁽²⁾	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

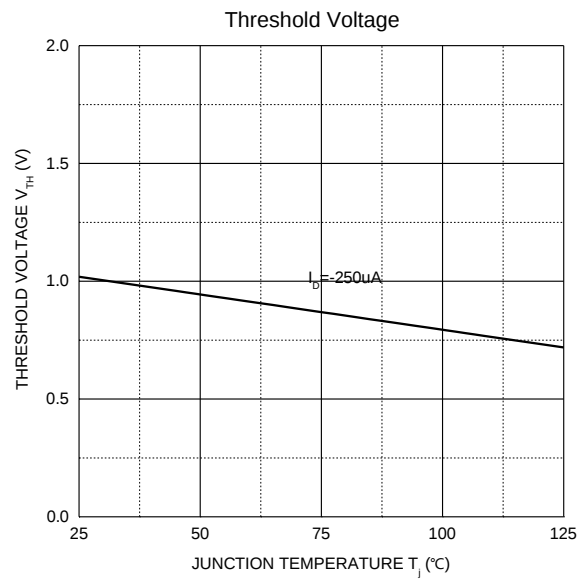
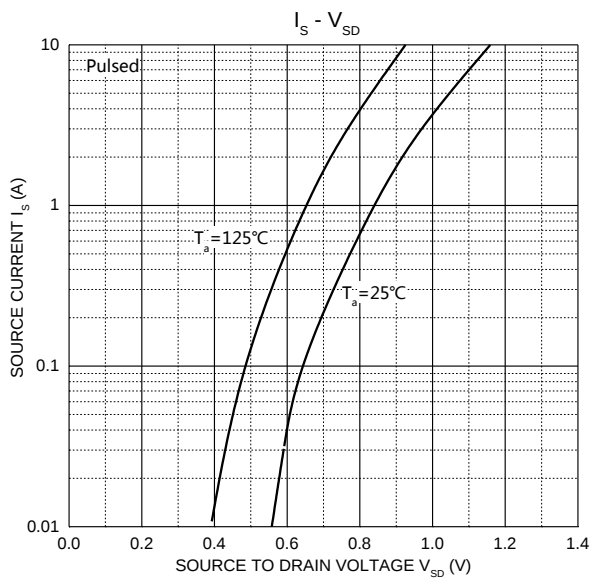
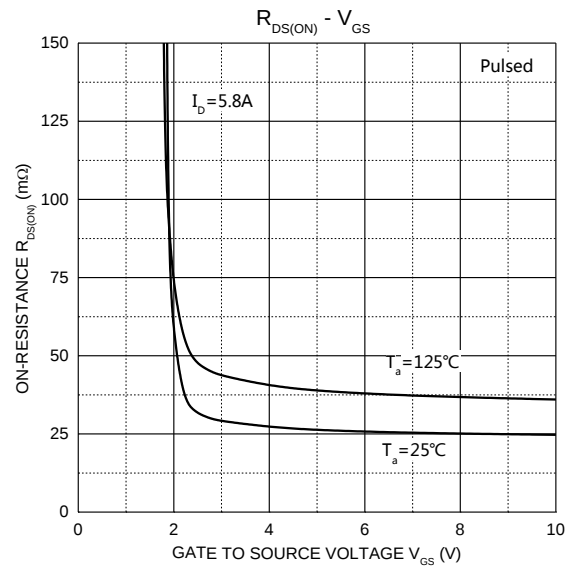
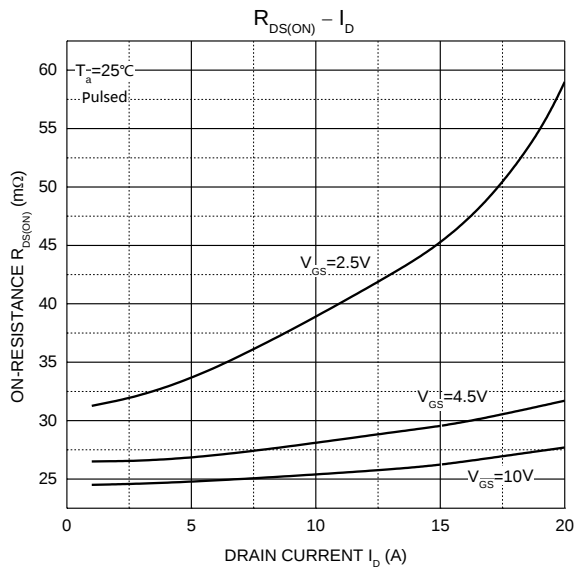
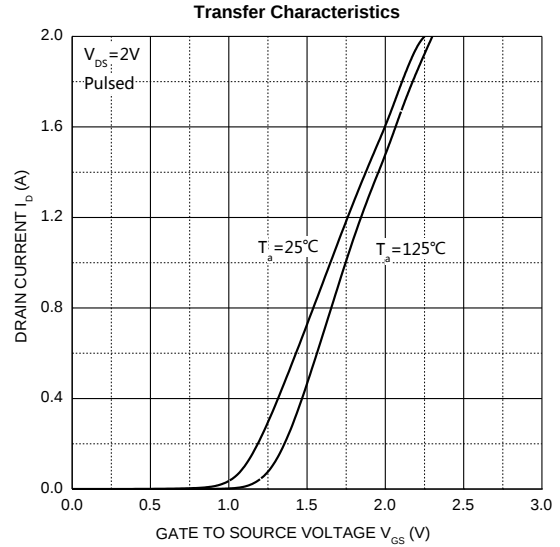
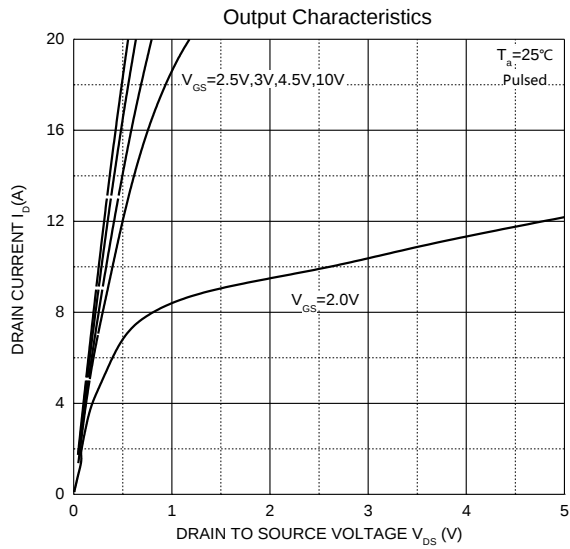
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V,V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±0.1	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7		1.4	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =5.8A		27	35	mΩ
		V _{GS} =4.5V, I _D =5A		29	40	
		V _{GS} =2.5V, I _D =4A		38	52	
Forward tranconductance	g _{FS}	V _{DS} =5V, I _D =5A	8			S
Dynamic characteristics ⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V,f =1MHz			1050	pF
Output Capacitance	C _{oss}			99		
Reverse Transfer Capacitance	C _{rss}			77		
Gate resistance	R _g	V _{DS} =0V,V _{GS} =0V, f =1MHz			3.6	Ω
Switching Characteristics ⁽⁴⁾						
Turn-on delay time	t _{d(on)}	V _{GS} =10V,V _{DS} =15V, R _L =2.7Ω,R _{GEN} =3Ω			5	ns
Turn-on rise time	t _r				7	
Turn-off delay time	t _{d(off)}				40	
Turn-off fall time	t _f				6	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =1A			1	V

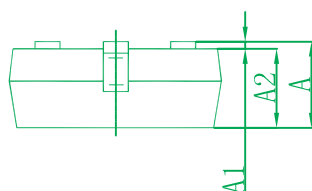
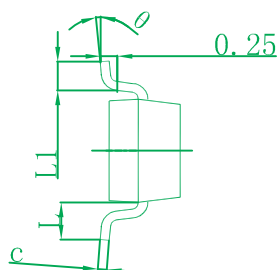
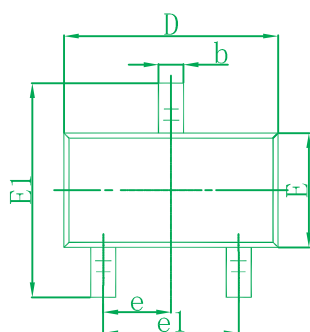
Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t < 5$ sec.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

Typical Electrical and Thermal Characteristics

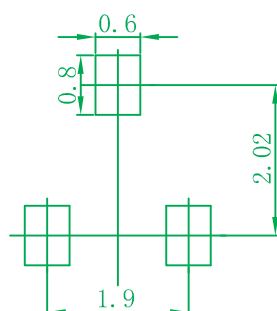


SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.150	0.035	0.045
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.050	0.110	0.120
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.360 REF		0.014 REF	
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

Ordering information

Device	Package	Shipping
EP3400	SOT-23	3000/Tape&Reel(7inches)